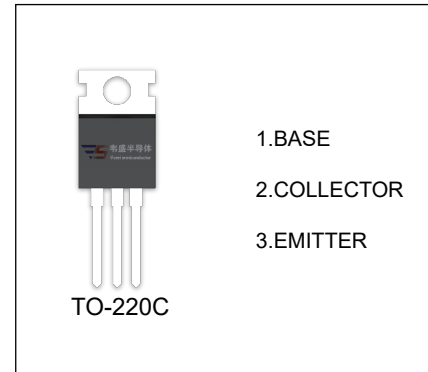


## 2SC2073 TRANSISTOR (NPN)

### FEATURES

- Wide safe Operating Area.
- Complementary to 2SA940



### MAXIMUM RATINGS ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	150	V
$V_{CEO}$	Collector-Emitter Voltage	150	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current -Continuous	1.5	A
$P_C$	Collector Power Dissipation	1.5	W
$T_J, T_{stg}$	Operation Junction and Storage Temperature Range	-55-150	$^{\circ}\text{C}$

### ELECTRICAL CHARACTERISTICS ( $T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}, I_E = 0$	150			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_B = 0$	150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}, I_C = 0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 120\text{V}, I_E = 0$			10	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$			10	$\mu\text{A}$
DC current gain	$h_{FE}$	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}$	40		140	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 0.5\text{A}, I_B = 50\text{mA}$			1.5	V
Base-emitter voltage	$V_{BE}$	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}$	0.65		0.85	V
Transition frequency	$f_T$	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}$		4		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		35		pF